Brewer Science[®] ProTEK[®] PSB

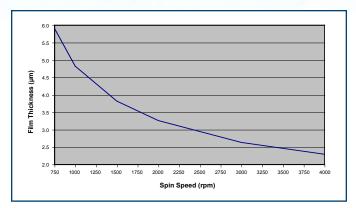
Photosensitive Alkaline-Resistant Protective Coating



Brewer Science® ProTEK® PSB coating is a negative-working photosensitive alkalineresistant etch mask that allows bulk silicon micromachining late in the device fabrication process while preserving the metal stack.

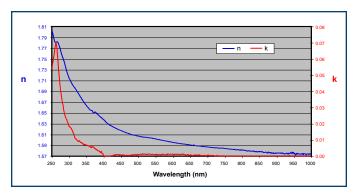
Benefits

- Apply over CMOS structures at low process temperatures
- Shorten processing time compared to SiN etch masks
- Provide higher throughput than single-wafer deep reactive ion etching by using batch processing



ProTEK® PSB-23 Coating Spin Speed Curve

ProTEK[®] PSB Coatings n & k Spectra



Processing Steps

Wafer Pretreatment (RCA 1 & RCA 2 Cleaning)

First Bath: $NH_4OH:H_2O_2:DI$ water (1:1:40) for 15 min at room temperature followed by DI water rinse at room temperature for 5 min

Second Bath: $HCI:H_2O_2:DI$ water (1:1:40) for 15 min at room temperature followed by DI water rinse at room temperature for 5 min

Spin rinse dry or dry wafers in oven at 70°C for ~ 2 hours

Process Parameters

ProTEK® PSB Primer (developmental) Coating Guidelines Spin Coat: 1000 rpm for 60 s,

Acceleration: > 1000 to 10,000 rpm/s First Bake (hot plate): 110°C for 60 s Second Bake (hot plate): 220°C for 5 min

ProTEK[®] PSB Protective Coating Guidelines Rinse wafer thoroughly with PGMEA and spin dry before applying ProTEK[®] PSB coating

Spin Coat ProTEK® PSB coating: 1500 rpm for 60 s, Acceleration: > 5000 rpm/s Bake (hot plate): 110 °C for 120 s

Exposure Guidelines (negative working)

Exposure Dose: 500 mJ/cm² i-line or broadband Post-Exposure Bake: 110°C for 120 s

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Development Guidelines

Spin Dispense or Spray (ethyl lactate *): 300 rpm for 10 s, Acceleration: 1000 rpm/s Spin Dry: 2000 rpm for 5 s, Acceleration: 10,000 rpm/s Repeat above development steps 2 to 4 times, as necessary

Spin Dispense or Spray (DI water or IPA): 300 rpm for 8 s, Acceleration: 1000 rpm/s Spin Dry: 2000 rpm for 40 s, Acceleration: 1000 rpm/s

Post-Development Guidelines

Post-Development Bake (hot plate): 220°C for 180 s

Etch in TMAH or KOH per customer process requirements

For optimal undercut performance: Recommended KOH bath temperature: ~ 75°C Recommended TMAH bath temperature: ~ 90°C

Removal Guidelines

100 mTorr

Recommended Dry Removal Process

- 1) Etch bulk film with O₂ plasma, 75 sccm O₂, 400 W, 75 mTorr
- 2) Etch with O₂:CF₄ (2:1), 56 sccm O₂, 19 sccm CF₄, 400 W,

Recommended Wet Removal Process

- Immerse wafers coated with ProTEK[®] PSB coating in Nano-Strip[®] from Cyantek^{**} for 30 minutes at 100°C
- 2) Rinse with DI water and dry

Storage Conditions

ProTEK[®] PSB Coatings: Room temperature (16°C to 26°C) ProTEK[®] PSB Primer: Room temperature (16°C to 26°C)

Shelf Life

ProTEK® PSB Coatings: 365 days ProTEK® PSB Primer (developmental): 270 days (When stored at conditions stated above)

*Ethyl lactate is not supplied by Brewer Scinece, Inc. Please contact your local chemical supplier for details on purchasing this material. **Nano-Strip® is manufactured and distributed by Cyantek. To purchase Nano-Strip®, please contact Cyantek at www.cyantek.com or phone +011.510.651.3341

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